

Test Report

日期(Date): 28-Apr-2023 號碼(No.): EKR22700419M01 頁數(Page): 1 of 17

日月光半導體製造股份有限公司 (ADVANCED SEMICONDUCTOR ENGINEERING INC.) 高雄市楠梓加工區內環北路107號 (26, CHIN 3 RD., 811, NANTZE EXPORT PROCESSING ZONE KAOHSIUNG TAIWAN.)

以下測試樣品係由申請廠商所提供及確認 (The following sample(s) was/were submitted and identified by the applicant as):

送樣廠商(Sample Submitted By) 日月光半導體製造股份有限公司 (ADVANCED SEMICONDUCTOR

ENGINEERING INC.)

樣品名稱(Sample Name) 12" 晶圓(WAFER)

樣品型號(Style/Item No.) 銅柱錫銀球 (Cu pillar SnAg BUMP, Cu layer+Ni layer +SnAg layer) 其他(Other Info.) 銅柱錫銀球 (Cu pillar SnAg BUMP, Cu layer+Ni layer +SnAg layer)

收件日(Sample Receiving Date)

07-Jul-2022

測試期間(Testing Period)

07-Jul-2022 to 13-Jul-2022

測試需求(Test Requested) :

(1) 依據客戶指定·參考RoHS 2011/65/EU Annex II及其修訂指令(EU) 2015/863測 試鎘、鉛、汞、六價鉻、多溴聯苯、多溴聯苯醚, DBP, BBP, DEHP, DIBP。(As specified by client, with reference to RoHS 2011/65/EU Annex II and amending Directive (EU) 2015/863 to determine Cadmium, Lead, Mercury, Cr(VI), PBBs, PBDEs, DBP, BBP, DEHP, DIBP contents in the submitted sample(s).)

(2) 其他測試項目請見下一頁。 (Please refer to next pages for the other item(s).) 請參閱下一頁 (Please refer to following pages.)

測試結果(Test Results)

論(Conclusion)

根據客戶所提供的樣品,其鎬、鉛、汞、六價鉻、多溴聯苯、多溴聯苯醚, DBP,

BBP, DEHP, DIBP的測試結果符合RoHS 2011/65/EU Annex II暨其修訂指令(EU) 2015/863之限值要求。 (Based on the performed tests on submitted sample(s), the test results of Cadmium, Lead, Mercury, Cr(VI), PBBs, PBDEs, DBP, BBP, DEHP, DIBP comply with the limits as set by RoHS Directive (EU)

2015/863 amending Annex II to Directive 2011/65/EU.)

Ray Chang, Ph.D./ Department Manage Signed for and on behalf SĞS TAIWAN LTD. 化學實驗室-高雄/Chemical Laboratory-Kaohsiung



PIN CODE: AE52854F



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測試部位敘述 (Test Part Description)

No.1 : 銀色 12" 晶圓(WAFER) (SILVER COLORED 12" 晶圓(WAFER))

測試結果 (Test Results)

測試項目	測試方法	單位	MDL	結果	限值
(Test Items)	(Method)	(Unit)		(Result)	(Limit)
				No.1	
鎘 (Cd) (Cadmium (Cd)) (CAS No.: 7440-	參考IEC 62321-5: 2013,以感應耦合電漿	mg/kg	2	n.d.	100
43-9)	發射光譜儀分析。(With reference to IEC				
	62321-5: 2013, analysis was performed				
	by ICP-OES.)				
鉛 (Pb) (Lead (Pb)) (CAS No.: 7439-92-1)	參考IEC 62321-5: 2013 · 以感應耦合電漿	mg/kg	2	n.d.	1000
	發射光譜儀分析。(With reference to IEC				
	62321-5: 2013, analysis was performed				
	by ICP-OES.)				
汞 (Hg) (Mercury (Hg)) (CAS No.: 7439-	参考IEC 62321-4: 2013+ AMD1: 2017・以	mg/kg	2	n.d.	1000
97-6)	感應耦合電漿發射光譜儀分析。(With reference to IEC 62321-4: 2013+ AMD1:				
	2017, analysis was performed by ICP-OES.)				
	, , , , , , , , , , , , , , , , , , ,				
六價鉻 Cr(VI) (Hexavalent Chromium	參考IEC 62321-7-2: 2017 · 以紫外光-可見	mg/kg	8	n.d.	1000
Cr(VI)) (CAS No.: 18540-29-9)	光分光光度計分析。(With reference to				
	IEC 62321-7-2: 2017, analysis was				
泊 歌 芝 (Manabramahinbanul)	performed by UV-VIS.)	/1	-	1	
一溴聯苯 (Monobromobiphenyl) 二溴聯苯 (Dibromobiphenyl)	-	mg/kg	5 5	n.d.	_
三溴聯苯 (Tribromobiphenyl)	ł	mg/kg	5	n.d. n.d.	-
四溴聯苯 (Tetrabromobiphenyl)	•	mg/kg	5	n.d.	_
五溴聯苯 (Pentabromobiphenyl)	參考IEC 62321-6: 2015 · 以氣相層析儀/質	mg/kg	5	n.d.	
六溴聯苯 (Hexabromobiphenyl)	譜儀分析。(With reference to IEC 62321-6: 2015, analysis was performed by GC/MS.)	mg/kg	5	n.d.	_
七溴聯苯 (Heptabromobiphenyl)		mg/kg	5		
八溴聯苯 (Octabromobiphenyl)		mg/kg	5	n.d. n.d.	-
九溴聯苯 (Nonabromobiphenyl)		mg/kg	5		_
十溴聯苯 (Decabromobiphenyl)		mg/kg	5	n.d.	-
多溴聯苯總和 (Sum of PBBs)		mg/kg		n.d.	1000
夕厌哪本総和 (SUIII OI PDDS)		mg/kg	-	n.d.	1000



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(Test Items)	(Method)	(Unit)		(Result)	(Limit)
				No.1	
一溴聯苯醚 (Monobromodiphenyl ether)		mg/kg	5	n.d.	-
二溴聯苯醚 (Dibromodiphenyl ether)		mg/kg	5	n.d.	=
三溴聯苯醚 (Tribromodiphenyl ether)		mg/kg	5	n.d.	=
四溴聯苯醚 (Tetrabromodiphenyl ether)	<u> </u>	mg/kg	5	n.d.	-
五溴聯苯醚 (Pentabromodiphenyl ether)	参考IEC 62321-6: 2015,以氣怕層析儀/質	mg/kg	5	n.d.	-
六溴聯苯醚 (Hexabromodiphenyl ether)	譜儀分析。(With reference to IEC 62321-6: 2015, analysis was performed by	mg/kg	5	n.d.	=
七溴聯苯醚 (Heptabromodiphenyl ether)	GC/MS.)	mg/kg	5	n.d.	=
八溴聯苯醚 (Octabromodiphenyl ether)	GC/IVI3.)	mg/kg	5	n.d.	=
九溴聯苯醚 (Nonabromodiphenyl ether)		mg/kg	5	n.d.	=
十溴聯苯醚 (Decabromodiphenyl ether)		mg/kg	5	n.d.	=
多溴聯苯醚總和 (Sum of PBDEs)		mg/kg	ı	n.d.	1000
銻 (Sb) (Antimony (Sb)) (CAS No.: 7440-36-0)	參考US EPA 3052: 1996.以感應耦合電漿 發射光譜儀分析。(With reference to US	mg/kg	2	n.d.	-
鈹 (Be) (Beryllium (Be)) (CAS No.: 7440-41-7)	 	mg/kg	2	n.d.	-
多氯聯苯 (PCBs) (Polychlorinated biphenyls (PCBs))	參考US EPA 3550C: 2007·以氣相層析儀/ 質譜儀分析。(With reference to US EPA 3550C: 2007, analysis was performed by GC/MS.)	mg/kg	0.5	n.d.	-
多氯奈 (PCNs) (Polychlorinated naphthalene (PCNs))	參考US EPA 3550C: 2007·以氣相層析儀/ 質譜儀分析。(With reference to US EPA 3550C: 2007, analysis was performed by GC/MS.)	mg/kg	5	n.d.	-
多氯三聯苯 (PCTs) (Polychlorinated terphenyls (PCTs))	參考US EPA 3550C: 2007·以氣相層析儀/ 質譜儀分析。(With reference to US EPA 3550C: 2007, analysis was performed by GC/MS.)	mg/kg	0.5	n.d.	-
短鏈氯化石蠟(C10-C13) (SCCP) (Short Chain Chlorinated Paraffins(C10-C13) (SCCP)) (CAS No.: 85535-84-8)	參考ISO 18219: 2015 · 以氣相層析儀/質譜儀分析。(With reference to ISO 18219: 2015, analysis was performed by GC/MS.)	mg/kg	50	n.d.	-



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測試項目	測試方法	單位	MDL	結果	限值
(Test Items)	(Method)	(Unit)		(Result)	(Limit)
				No.1	
氟 (F) (Fluorine (F)) (CAS No.: 14762-94-		mg/kg	50	n.d.	-
8)					
氯 (CI) (Chlorine (CI)) (CAS No.: 22537-	参考BS EN 14582: 2016,以離子層析儀分	mg/kg	50	n.d.	-
15-1)	析。(With reference to BS EN 14582:				
溴 (Br) (Bromine (Br)) (CAS No.: 10097-	2016, analysis was performed by IC.)	mg/kg	50	n.d.	-
32-2)					
碘 (I) (Iodine (I)) (CAS No.: 14362-44-8)		mg/kg	50	n.d.	-
三丁基錫 (TBT) (Tributyl tin (TBT))	參考ISO 17353: 2004 · 以氣相層析儀/火	mg/kg	0.03	n.d.	-
三苯基錫 (TPT) (Triphenyl tin (TPT))	焰光度偵測器分析。(With reference to	mg/kg	0.03	n.d.	-
二丁基錫 (DBT) (Dibutyl tin (DBT))	ISO 17353: 2004, analysis was	mg/kg	0.03	n.d.	-
二辛基錫 (DOT) (Dioctyl tin (DOT))	performed by GC/FPD.)	mg/kg	0.03	n.d.	-
氧化雙三丁基錫 (TBTO) (Bis(tributyItin)	由三丁基錫測試結果計算得之。	mg/kg	0.03 🛦	n.d.	-
oxide (TBTO)) (CAS No.: 56-35-9)	(Calculated from the result of Tributyl				
	Tin (TBT).)				
全氟辛烷磺酸及其鹽類 (PFOS and its	**************************************	mg/kg	0.01	n.d.	-
salts) (CAS No.: 1763-23-1 and its salts)	參考CEN/TS 15968: 2010·以液相層析串 聯質譜儀分析。(With reference to				
全氟辛酸 (PFOA)及其鹽類	所具語 譲力が	mg/kg	0.01	n.d.	-
(Perfluorooctanoic acid (PFOA) and it's	performed by LC/MS/MS.)				
salt) (CAS No.: 335-67-1 and its salts)	performed by Ee/Wi3/Wi3.				
六溴環十二烷及所有主要被辨別出的異構	參考IEC 62321: 2008·以氣相層析儀/質譜	mg/kg	5	n.d.	-
物(HBCDD) (α- HBCDD, β- HBCDD, γ-	儀分析。(With reference to IEC 62321:				
HBCDD) (Hexabromocyclododecane	2008, analysis was performed by				
(HBCDD) and all major	GC/MS.)				
diastereoisomers identified (α - HBCDD,					
β- HBCDD, γ- HBCDD)) (CAS No.:					
25637-99-4, 3194-55-6 (134237-51-7,					
134237-50-6, 134237-52-8))					
聚氯乙烯 (Polyvinyl chloride) (PVC)	參考ASTM E1252: 2013 · 以傅立葉轉換紅	**	-	Negative	-
	外線光譜儀及焰色法分析。(With				
	reference to ASTM E1252: 2013, analysis				
	was performed by FT-IR and Flame Test.)				



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測試項目 (Test Items)	測試方法 (Method)	單位 (Unit)	MDL	結果 (Result)	限值 (Limit)
(rest items)	(Wicthod)	(Onit)		No.1	(Liiiit)
鄰苯二甲酸丁苯甲酯 (BBP) (Butyl benzyl phthalate (BBP)) (CAS No.: 85-68-7)	參考IEC 62321-8: 2017 · 以氣相層析儀/質譜儀分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50	n.d.	1000
鄰苯二甲酸二丁酯 (DBP) (Dibutyl phthalate (DBP)) (CAS No.: 84-74-2)	參考IEC 62321-8: 2017 · 以氣相層析儀/質譜儀分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50	n.d.	1000
鄰苯二甲酸二(2-乙基己基)酯 (DEHP) (Di-(2-ethylhexyl) phthalate (DEHP)) (CAS No.: 117-81-7)	參考IEC 62321-8: 2017·以氣相層析儀/質譜儀分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50	n.d.	1000
鄰苯二甲酸二異丁酯 (DIBP) (Diisobutyl phthalate (DIBP)) (CAS No.: 84-69-5)	參考IEC 62321-8: 2017·以氣相層析儀/質譜儀分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50	n.d.	1000
鄰苯二甲酸二異癸酯 (DIDP) (Diisodecyl phthalate (DIDP)) (CAS No.: 26761-40-0, 68515-49-1)	參考IEC 62321-8: 2017·以氣相層析儀/質譜儀分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50	n.d.	-
鄰苯二甲酸二異壬酯 (DINP) (Diisononyl phthalate (DINP)) (CAS No.: 28553-12-0, 68515-48-0)	參考IEC 62321-8: 2017·以氣相層析儀/質譜儀分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50	n.d.	-
` '`	參考IEC 62321-8: 2017·以氣相層析儀/質譜儀分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50	n.d.	-



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備註(Note):

- 1. mg/kg = ppm; 0.1wt% = 0.1% = 1000ppm
- 2. MDL = Method Detection Limit (方法偵測極限值)
- 3. n.d. = Not Detected (未檢出); 小於MDL / Less than MDL
- 4. "-" = Not Regulated (無規格值)
- 5. **= Qualitative analysis (No Unit) 定性分析(無單位)
- 6. Negative = Undetectable 陰性(未偵測到); Positive = Detectable 陽性(已偵測到)
- 7. 全氟辛烷磺酸及其鹽類包含 (PFOS and its salts including):
 - CAS No.: 29081-56-9, 2795-39-3, 29457-72-5, 70225-14-8, 56773-42-3, 251099-16-8, 307-35-7.
- 8. 全氟辛酸及其鹽類包含 (PFOA and its salts including):
 - CAS No.: 3825-26-1, 335-95-5, 2395-00-8, 335-93-3, 335-66-0.
- 9. ▲: MDL是針對元素/測試化合物之評估。(The MDL was evaluated for element / tested substance.) 換算公式 (Conversion Formula): AX = A × F

AX	A	F
氧化雙三丁基錫 (Bis(tributyltin)oxide) (TBTO)	三丁基錫 (Tributyl Tin) (TBT)	1.0276

參數換算表 (Parameter Conversion Table):

https://eecloud.sgs.com/Region_TW/DocDownload.aspx#otherDoc

- 10. 除非另有說明·參照ILAC-G8:09/2019·採用簡單二元(w=0)允收規則進行符合性判定;根據此規則·符合性結果之判定係以測試結果與限值做比較。(Unless otherwise stated, the decision rule for conformity reporting is based on Binary Statement for Simple Acceptance Rule (w=0) stated in ILAC-G8:09/2019. According to this rule, the judgement of conformity is based on the comparing test results with limits.)
- 11. 本報告為 EKR22700419 之異動報告。(This is the additional test report of EKR22700419.)



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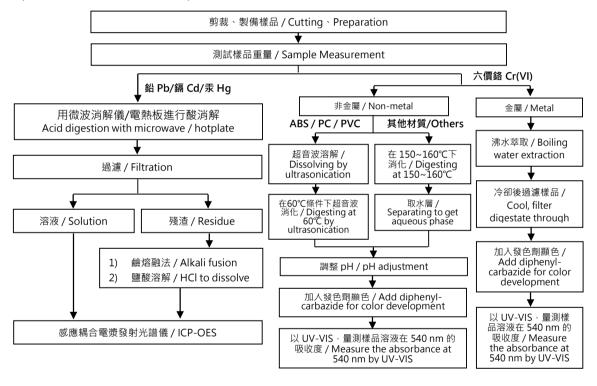
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重金屬流程圖 / Analytical flow chart of Heavy Metal

根據以下的流程圖之條件,樣品已完全溶解。(六價鉻測試方法除外)

These samples were dissolved totally by pre-conditioning method according to below flow chart. (Cr^{6+} test method excluded)





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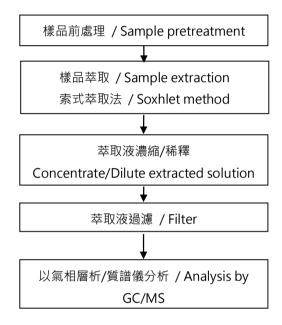
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多溴聯苯/多溴聯苯醚 分析流程圖 / PBB/PBDE analytical FLOW CHART





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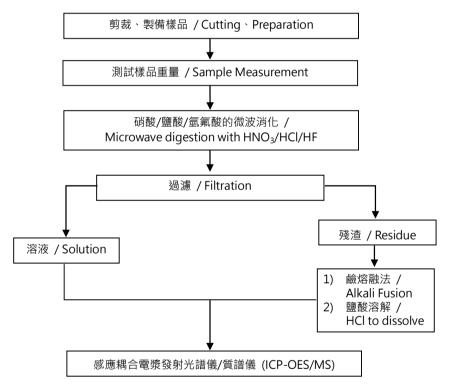
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元素(含重金屬)分析流程圖 / Analytical flow chart of Elements (Heavy metal included)

根據以下的流程圖之條件,樣品已完全溶解。

These samples were dissolved totally by pre-conditioning method according to below flow chart.

【參考方法/Reference method: US EPA 3051、US EPA 3052】



* US EPA 3051 方法未添加氫氟酸 / US EPA 3051 method does not add HF.



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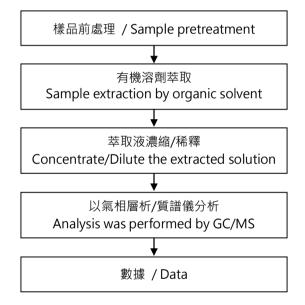
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分析流程圖 / Analytical flow chart

【適用於:多氯聯苯、多氯奈、多氯三聯苯、滅蟻靈、氯化石蠟、DBBT】

*Apply to: PCBs, PCNs, PCTs, Mirex, Chlorinated Paraffins, DBBT





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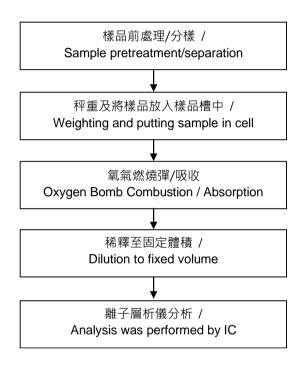
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鹵素分析流程圖 / Analytical flow chart of Halogen





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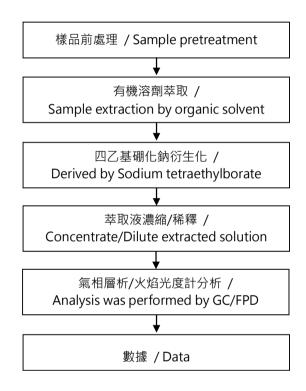
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有機錫分析流程圖 / Analytical flow chart - Organic-Tin





Test Report

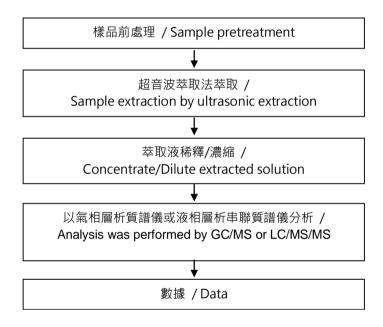
號碼(No.): EKR22700419M01

日期(Date): 28-Apr-2023

頁數(Page): 13 of 17

日月光半導體製造股份有限公司 (ADVANCED SEMICONDUCTOR ENGINEERING INC.) 高雄市楠梓加工區內環北路107號 (26, CHIN 3 RD., 811, NANTZE EXPORT PROCESSING ZONE KAOHSIUNG TAIWAN.)

全氟化合物(包含全氟辛酸/全氟辛烷磺酸/其相關化合物等等)分析流程圖 / Analytical flow chart – PFAS (including PFOA/PFOS/its related compound, etc.)





Test Report

號碼(No.): EKR22700419M01

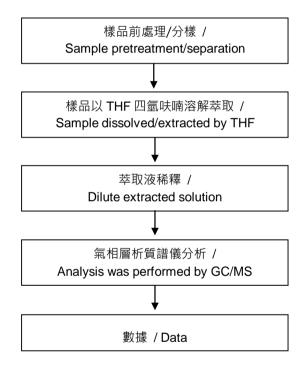
日期(Date): 28-Apr-2023

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日月光半導體製造股份有限公司 (ADVANCED SEMICONDUCTOR ENGINEERING INC.) 高雄市楠梓加工區內環北路107號 (26, CHIN 3 RD., 811, NANTZE EXPORT PROCESSING ZONE KAOHSIUNG TAIWAN.)

可塑劑分析流程圖 / Analytical flow chart of phthalate content

【測試方法/Test method: IEC 62321-8】



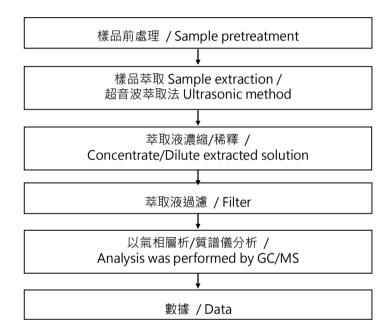


Test Report

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六溴環十二烷分析流程圖 / Analytical flow chart - HBCDD





Test Report

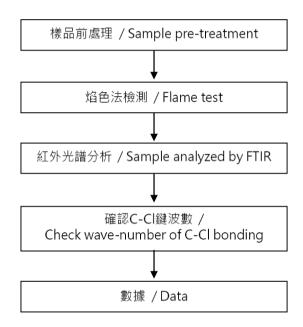
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聚氯乙烯物質判定分析流程圖 / Analysis flow chart - PVC





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號碼(No.): EKR22700419M01

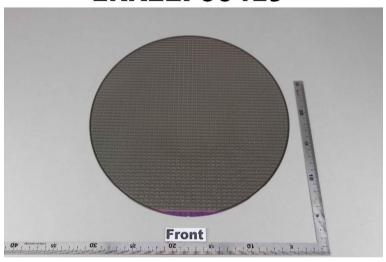
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* 照片中如有箭頭標示,則表示為實際檢測之樣品/部位. * (The tested sample / part is marked by an arrow if it's shown on the photo.)

EKR22700419



EKR22700419



** 報告結尾 (End of Report) **